

DMNH15H110SPS

150V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

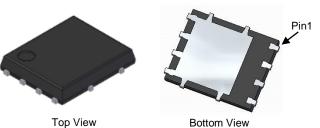
BV _{DSS}	Rds(on) Max	I⊳ Max Tc = +25°C
150V	90mΩ @ V _{GS} = 10V	27A
	100mΩ @ Vgs = 6V	26A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- **Engine Management Systems**
- **Body Control Electronics**
- **DC/DC** Converters

PowerDI5060-8



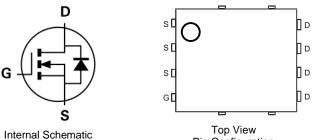
Top View

Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_q Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/guality/product-definitions/

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208(03)
- Weight: 0.097 grams (Approximate)



Pin Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMNH15H110SPS-13	PowerDI5060-8	2500/Tape & Reel

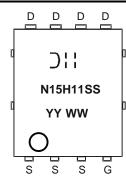
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:



⊃¦¦ = Manufacturer's Marking N15H11SS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 20 = 2020)WW = Week (01 to 53)



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			VDSS	150	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 7) V _{GS} = 10V	Steady State	Tc = +25°C Tc = +100°C	lo	27 19	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	IDM	108	A		
Maximum Continuous Body Diode Forward Current (Note 7)			ls	27	A
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)			lsм	108	A
Avalanche Current (Note 8) L = 3mH			las	9	A
Avalanche Energy (Note 8) L = 3mH			E _{AS}	121.5	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	PD	1.5	W	
Thermal Resistance, Junction to Ambient (Note 5)	RθJA	98	°C/W	
Total Power Dissipation (Note 6)	PD	3.4	W	
Thermal Resistance, Junction to Ambient (Note 6)	RθJA	44	°C/W	
Thermal Resistance, Junction to Case (Note 7)	Rejc	1.5		
Operating and Storage Temperature Range	TJ, TSTG	-55 to +175	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BVDSS	150	_	—	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	IDSS		—	1	μA	V _{DS} = 120V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	2	—	4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Descent		70	90	~ 0	$V_{GS} = 10V, I_D = 2A$	
	RDS(ON)		76	100	mΩ	$V_{GS} = 6V, I_D = 2A$	
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	$V_{GS} = 0V$, $I_S = 2A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss		989	_	pF	− V _{DS} = 75V, V _{GS} = 0V, − f = 1MHz	
Output Capacitance	Coss		63	—	pF		
Reverse Transfer Capacitance	Crss		38.3	_	pF		
Gate Resistance	Rg		1.3	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz	
Total Gate Charge (V _{GS} = 10V)	Qg		25.5	—	nC		
Total Gate Charge (V _{GS} = 6V)	Qg		17.8	_	nC		
Gate-Source Charge	Q _{gs}	_	4.0	—	nC	$-V_{DS} = 75V, I_{D} = 4A$	
Gate-Drain Charge	Qgd	_	10	_	nC	7	
Turn-On Delay Time	tD(ON)	_	18	_	ns		
Turn-On Rise Time	tR		46	_	ns	$V_{DD} = 75V, V_{GS} = 10V$ $R_G = 24\Omega, I_D = 4A$	
Turn-Off Delay Time	tD(OFF)		76	—	ns		
Turn-Off Fall Time	tF		59	_	ns		
Reverse Recovery Time	trr	I	42	_	ns		
Reverse Recovery Charge	Qrr	_	66	_	nC	I _F = 4A, di/dt=100A/μs	

Notes:

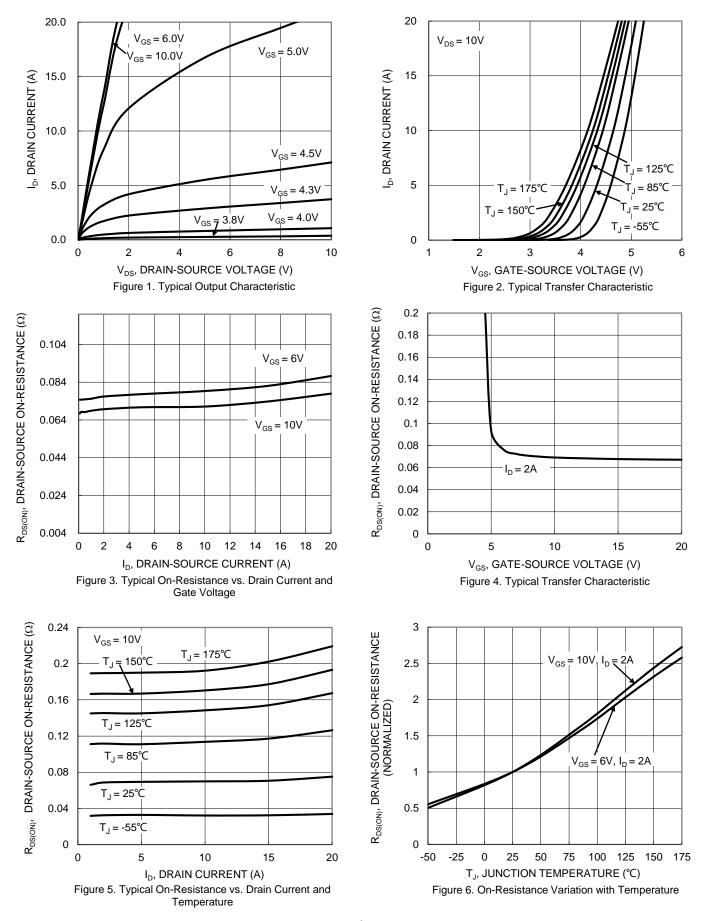
Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

7. Thermal resistance from junction to soldering point (on the exposed drain pad).

8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$. 9. Short duration pulse test used to minimize self-heating effect. 10. Guaranteed by design. Not subject to product testing.



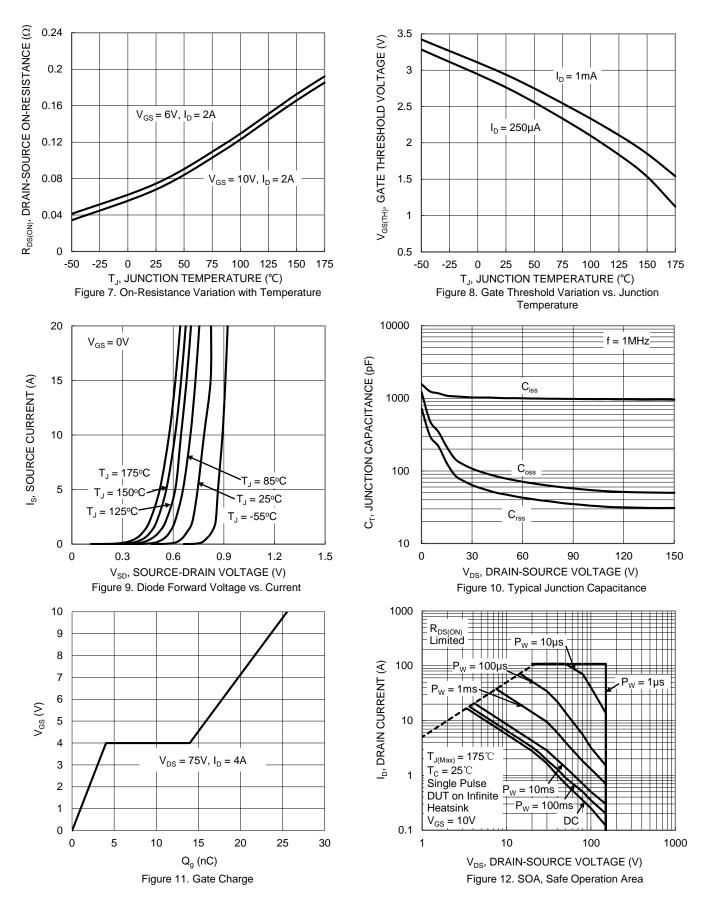
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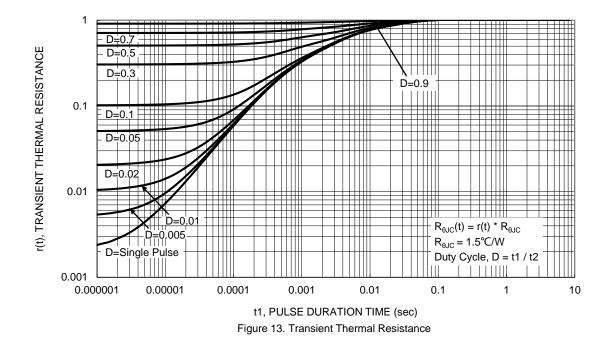


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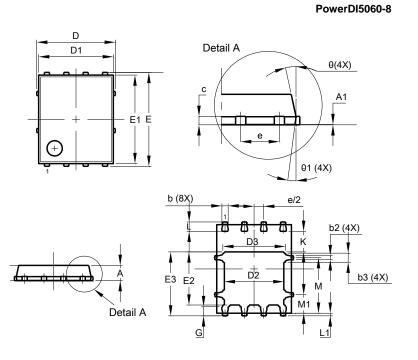






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

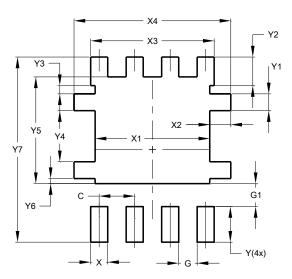


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
c	0.230	0.330	0.277		
D		5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
E	6.15 BSC				
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
Μ	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610



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